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# 10V Drive Nch MOSFET

# **RK3055E**

#### Structure

Silicon N-channel MOSFET

#### ● Features

- 1) Low On-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) 10V drive.
- 5) Drive circuits can be simple.
- 6) Parallel use is easy.

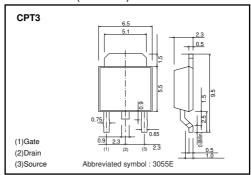
#### Applications

Switching

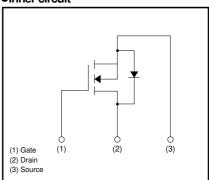
## Packaging specifications

Туре	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	2500
RK3055E		0

#### ● Dimensions (Unit: mm)



#### •Inner circuit



## ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	60	V
Gate-source voltage		Vgss	±20	V
Duain accurant	Continuous	lo	8	Α
Drain current	Pulsed	IDP*	20	Α
Reverse drain	Continuous	Idr	8	Α
current	Pulsed	IDRP*	20	А
Total power dissipation (Tc=25°C)		PD	20	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

<sup>\*</sup> Pw≤10μs, Duty cycle≤1%

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#### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Gate-source leakage	Igss	-	_	±100	nA	Vgs=±20V, Vds=0V
Drain-source breakdown voltage	V(BR)DSS	60	_	_	V	In=1mA, Vgs=0V
Zero gate voltage drain current	IDSS	-	_	10	μΑ	VDS=60V, VGS=0V
Gate threshold voltage	V <sub>GS(th)</sub>	1.0	_	2.5	V	VDS=10V, ID=1mA
Static drain-source on-state resistance	RDS(on)	-	_	0.15	Ω	In=4A, Vgs=10V
Forward transfer admittance	Y <sub>fs</sub>   *	4.0	_	_	S	ID=4A, VDS=15V
Input capacitance	Ciss	-	520	-	pF	V <sub>DS</sub> =10V
Output capacitance	Coss	_	240	-	pF	V <sub>G</sub> =0V
Reverse transfer capacitance	Crss	-	100	-	pF	f=1MHz
Turn-on delay time	td(on)	_	5.0	-	ns	I <sub>D</sub> =2.5A, V <sub>DD</sub> ≒ 30V
Rise time	tr	-	20	_	ns	V <sub>GS</sub> =10V
Turn-off delay time	td(off)	_	50	-	ns	RL=12Ω
Fall time	tf		20	_	ns	R <sub>G</sub> =10Ω

<sup>\*</sup> Pw  $\leq 300 \mu s$ , Duty cycle  $\leq 1\%$ 

#### •Electrical characteristics curve

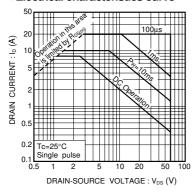


Fig.1 Maximum Safe Operating Area

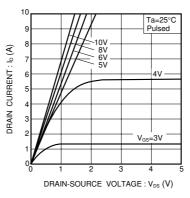


Fig.2 Typical Output Characteristics

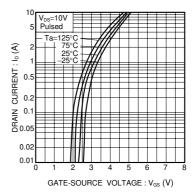


Fig.3 Typical Transfer Characteristics

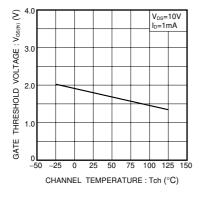


Fig.4 Gate Threshold Voltage vs. Channel Temperature

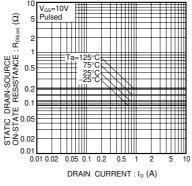


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current ( I )

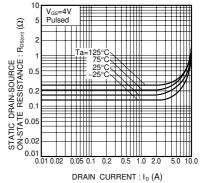
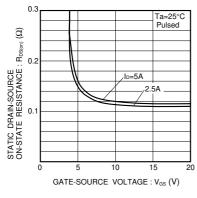


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current ( II )



0.6 V<sub>SS</sub>=10V Pulsed

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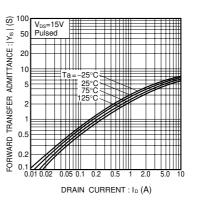
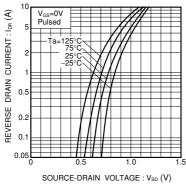


Fig.7 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

Fig.8 Static Drain-Source On-State Resistance vs. Channel Temperature

Fig.9 Forward Transfer Admittance vs. Drain Current





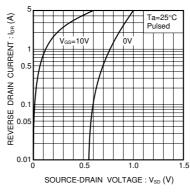


Fig.11 Reverse Drain Current vs. Source-Drain Voltage ( II )

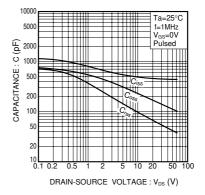


Fig.12 Typical Capacitance vs. Drain-Source Voltage

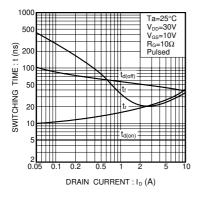


Fig.13 Switching Characteristics (See Figures 16 and 17 for the measurement circuit and resultant waveforms)

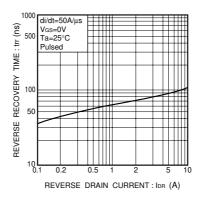


Fig.14 Reverse Recovery Time vs. Reverse Drain Current

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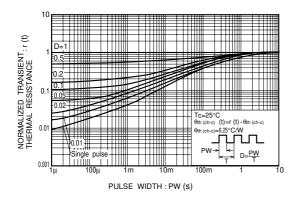
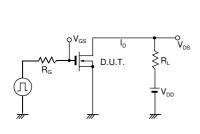


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

## •Switching characteristics measurement circuit



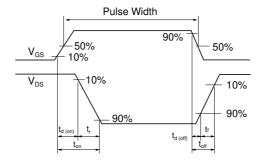


Fig.16 Switching Time Test Circuit

Fig.17 Switching Time Waveforms

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